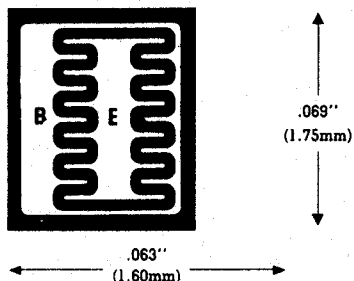


CHIP NUMBER

269



Base: .009" x .050" (0.23mm x 1.27mm)
 Emitter: .009" x .042" (0.23mm x 1.07mm)

PNP EPITAXIAL PLANAR POWER TRANSISTOR** (FORMERLY 69)

CONTACT METALLIZATION

Base and emitter: > 30,000 Å Aluminum

Collector: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .140" Diameter (3.56mm)

Thickness: .010" (0.25mm)

BeO PEDESTAL

Size: .142" x .178" (3.61mm x 4.52mm)

Thickness: .023" (0.58mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the chip be eutectically mounted with gold silicon preform 98/2%.

b) 8 mil (0.203mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 269 in a TO-66 or equivalent case:

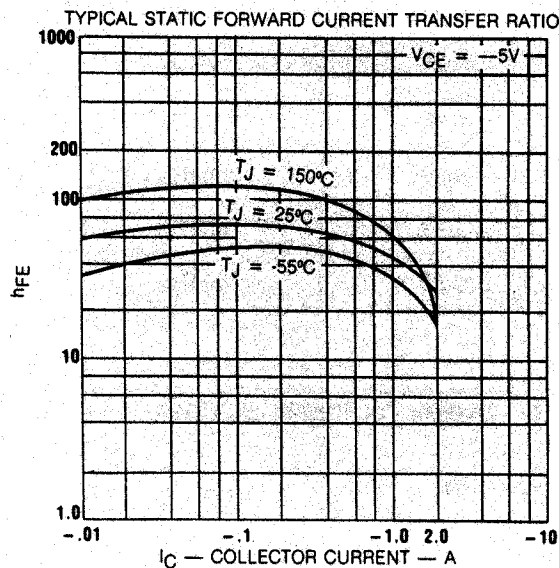
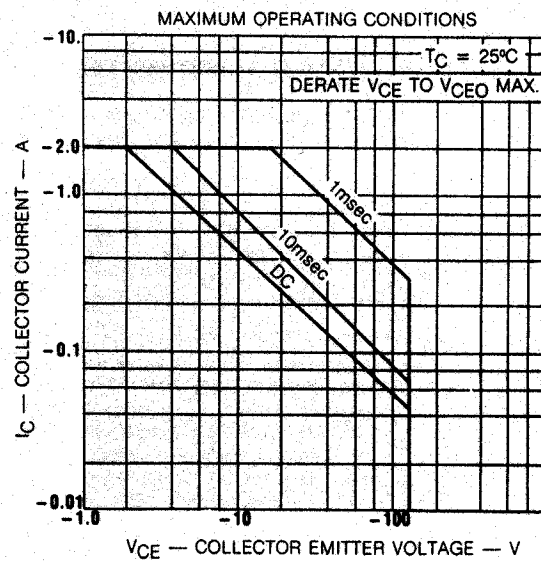
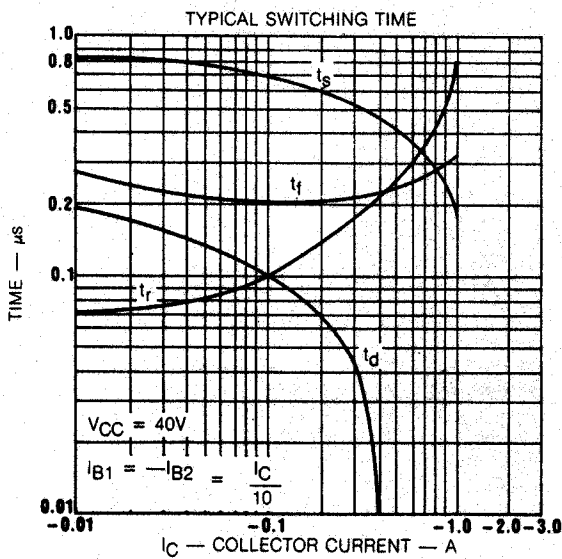
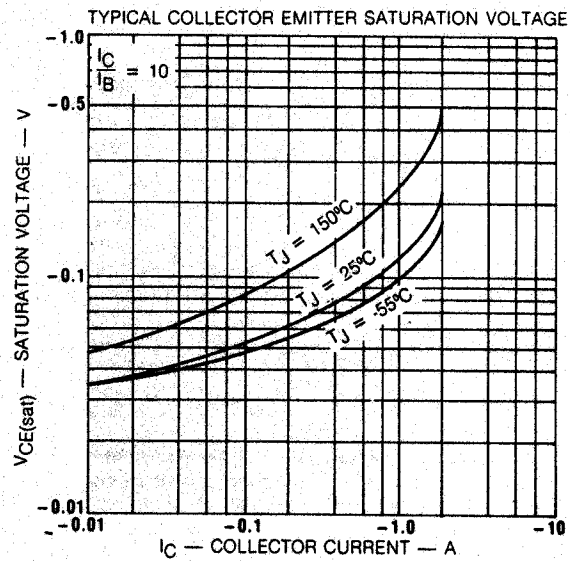
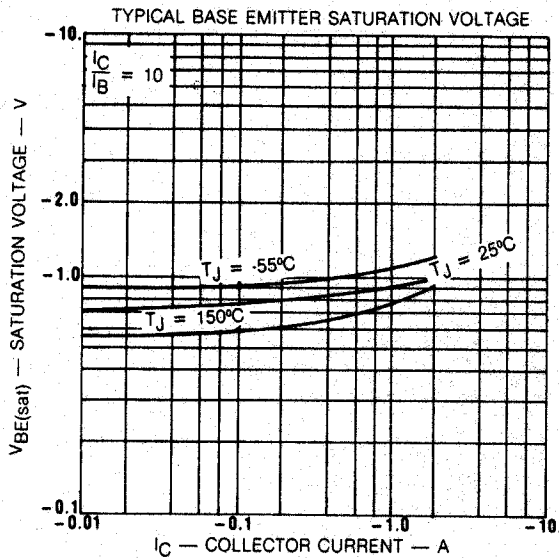
V _{CEO}	V _{CE(s)} @	I _C	I _B	h _{FE} @	I _C	V _{CE}
> 60V	< 0.35V	0.5A	50mA	> 15	2A	5V
> 80V	< 0.35V	0.5A	50mA	> 15	2A	5V
> 100V	< 0.35V	0.5A	50mA	> 15	2A	5V
* > 150V	< 0.35V	0.5A	50mA	> 5	2A	5V
* > 200V	< 0.35V	0.5A	50mA	> 5	2A	5V

V _{CEO}	V _{CEX}	V _{EBO}	f _T	C _{OBO}	θ _{JC}
> 60V	70V	> 5V	40MHz	< 60pF	< 25°C/W
> 80V	90V	> 5V	40MHz	< 60pF	< 25°C/W
> 100V	110V	> 5V	40MHz	< 60pF	< 25°C/W
> 150V	160V	> 5V	40MHz	< 60pF	< 25°C/W
> 200V	210V	> 5V	40MHz	< 60pF	< 25°C/W

TYPICAL DEVICE TYPES: JAN2N3740, JAN2N3741, SDT69601 - SDT69613, SDT69501 - SDT69513

*h_{FE} available at I_C = 500mA, V_{CE} = 5V, > 20

**The respective NPN complement is chip number 191.



NOTE:
PERFORMANCE CURVES
REPRESENT LOW TO
MIDDLE V_{CE0} VOLTAGE
RANGE OF THIS PRODUCT